

# SSDM 2006 Time Table

## Wednesday, September 13

### MAIN HALL

10:00-12:20 PL: Opening Session/SSDM & Paper Award

Room 411/412 (A)	Room 413 (B)	Room 414/415 (C)	Room 416/417 (D)	Room 418 (E)	Room 419 (F)	Room 501 (G)	Room 502 (H)	Room 511/512 (I)	Small Auditorium (J)
14:00-15:45 Area 9: Physics and Applications of Novel Functional Materials and Devices A-1: Novel Devices and Characterization	14:00-16:00 Area 7: Photonic Devices and Device Physics B-1: Special Session : Photonic Crystals and Si Photonics I	14:00-16:20 Area 5: Advanced Circuits and Systems C-1: MEMS and Modeling	14:00-15:30 Area 10: Organic Materials Science, Device Physics, and Applications D-1: Organic Light Emitting Diodes	14:00-15:45 Area 6: Compound Semiconductor Circuits, Electron Devices and Device Physics E-1: High-Speed Devices and ICs	14:00-15:50 Area 4: Advanced Memory Technology F-1: FeRAM	14:00-15:50 Area 2: Characterization and Materials Engineering for Interconnect Integration G-1: Advanced Metallization	14:00-16:00 Area 3: CMOS Devices /Device Physics H-1: CMOS Performance Enhancement Technology I	14:00-15:45 Area 8: Advanced Material Synthesis and Crystal Growth Technology I-1: Nanostructure Fabrication	14:00-16:00 Area 1: Advanced Gate Stack /Si Processing Science J-1: Metal/High-k Gate Stack
16:15-18:00 Area 9: Physics and Applications of Novel Functional Materials and Devices A-2: Novel Optical Devices	16:15-18:00 Area 7: Photonic Devices and Device Physics B-2: Special Session : Photonic Crystals and Si Photonics II	16:30-18:10 Area 5: Advanced Circuits and Systems C-2: Wireless Interconnect	16:00-17:45 Area 10: Organic Materials Science, Device Physics, and Applications D-2: Organic Light Emitting Diodes and Solar Cells	16:15-17:45 Area 6: Compound Semiconductor Circuits, Electron Devices and Device Physics E-2: Wide-Bandgap Devices	16:15-18:00 Area 4: Advanced Memory Technology F-2: DRAM	16:15-18:00 Area 2: Characterization and Materials Engineering for Interconnect Integration G-2: Characterization I	16:15-18:00 Area 3: CMOS Devices /Device Physics H-2: CMOS Performance Enhancement Technology II	16:15-18:00 Area 8: Advanced Material Synthesis and Crystal Growth Technology I-2: Compound Semiconductors	16:15-18:00 Area 1: Advanced Gate Stack /Si Processing Science J-2: FUSI Gate Electrode

18:30-20:30 Banquet/Young Award (Intercontinental Hotel, Pacific 3F)

## Thursday, September 14

Room 411/412 (A)	Room 413 (B)	Room 414/415 (C)	Room 416/417 (D)	Room 418 (E)	Room 419 (F)	Room 501 (G)	Room 502 (H)	Room 511/512 (I)	Small Auditorium (J)
9:00-10:30 Area 11: Micro/nano Electromechanical and Bio-Systems (Devices) A-3 : MEMS and NEMS : Fabrication	9:00-10:30 Area 7: Photonic Devices and Device Physics B-3 : LEDs and Lasers	9:00-10:20 Area 5: Advanced Circuits and Systems C-3: Toward Next Generation Systems	9:00-10:30 Area 10: Organic Materials Science, Device Physics, and Applications D-3: Organic Materials and Device Physics I	9:00-10:00 Area 6: Compound Semiconductor Circuits, Electron Devices and Device Physics E-3: Sensors and Interface Physics	9:00-10:40 Area 3: CMOS Devices /Device Physics F-3: Quasi-Ballistic Transport	(Poster setting)	(Poster setting)	(Poster setting)	9:10-10:40 Area 1: Advanced Gate Stack /Si Processing Science J-3: Characterization of Gate Stack
10:45-12:15 Short Presentation Area 11 and Area 8	10:45-12:15 Short Presentation Area 7 and Area 4	10:45-12:15 Short Presentation Area 5 and Area 2	10:45-11:30 Area 10: Organic Materials Science, Device Physics, and Applications D-4: Organic Materials and Device Physics II 11:30-12:30 Short Presentation Area 10	10:45-12:15 Short Presentation Area 6 and Area 9	10:45-12:15 Short Presentation Area 3	(Poster setting)	(Poster setting)	(Poster setting)	10:45-12:15 Short Presentation Area 1

13:00-15:00 Poster Session

15:15-16:15 Joint Area 8 and 9 A-5: Nanowires and Nanotubes I	15:15-16:30 Area 7: Photonic Devices and Device Physics B-5: Quantum-dot Lasers	15:15-16:25 Area 4: Advanced Memory Technology C-5: ReRAM	15:15-16:15 Area 2: Characterization and Materials Engineering for Interconnect Integration D-5: Emerging Interconnect	15:15-16:35 Area 1: Advanced Gate Stack/ Si Processing Science E-5: Junction I	15:15-16:35 Area 3: CMOS Devices /Device Physics F-5: Device Fluctuation Analysis	(Poster removed by 15:30 and Preparation for Rump Session)	(Poster removed by 15:30 and Preparation for Rump Session)	(Poster removed)	15:15-16:35 Area 1: Advanced Gate Stack /Si Processing Science J-5: High-k Dielectrics I
16:30-18:00 Joint Area 8 and 9 A-6: Nanowires and Nanotubes II	16:45-18:00 Area 7: Photonic Devices and Device Physics B-6: Quantum Optical Devices	16:45-17:55 Area 4: Advanced Memory Technology C-6: Flash Memory I	16:25-17:45 Area 2: Characterization and Materials Engineering for Interconnect Integration D-6: Assembly and Packaging	16:45-17:45 Area 1: Advanced Gate Stack/ Si Processing Science E-6: Junction II	16:45-18:05 Area 3: CMOS Devices /Device Physics F-6: Device Reliability and Characterization	(Poster removed by 15:30 and Preparation for Rump Session)	(Poster removed by 15:30 and Preparation for Rump Session)	16:45-18:05 Area 5: Advanced Memory Technology I-6: Analog Circuit Techniques	16:45-17:45 Area 1: Advanced Gate Stack /Si Processing Science J-6: Interface Properties of Ge

18:30-20:30 Rump Session Room 501 "Challenges of New Non-Volatile Memories : Innovative Strategies to catch up with FLASH"  
Room 502 "Nanotechnology - Impact on Electronics, Photonics and Biology-"

## Friday, September 15

Room 411/412 (A)	Room 413 (B)	Room 414/415 (C)	Room 416/417 (D)	Room 418 (E)	Room 419 (F)	Room 501 (G)	Room 502 (H)	Room 511/512 (I)	Small Auditorium (J)
9:00-10:30 Area 9: Physics and Applications of Novel Functional Materials and Devices A-7: Novel Devices and Materials I	9:00-10:30 Area 7: Photonic Devices and Device Physics B-7: Micro-Optics and Optical Waveguides	9:00-10:30 Area 11: Micro/nano Electromechanical and Bio-Systems (Devices) C-7: Micro and Nano Fluidics for Biosensing	9:45-10:30 Area 10: Organic Materials Science, Device Physics, and Applications D-7: Molecular Electronics		9:00-10:20 Area 4: Advanced Memory Technology F-7: Flash Memory II	9:00-10:40 Area 2: Characterization and Materials Engineering for Interconnect Integration G-7: Characterization II	9:00-10:40 Area 3: CMOS Devices /Device Physics H-7: Compact Modeling	9:00-10:15 Area 8: Advanced Material Synthesis and Crystal Growth Technology I-7: Novel Materials	9:00-10:40 Area 1: Advanced Gate Stack /Si Processing Science J-7: High-k Dielectrics II
10:45-12:15 Area 9: Physics and Applications of Novel Functional Materials and Devices A-8: Novel Devices and Materials II	10:45-12:00 Area 7: Photonic Devices and Device Physics B-8: All-Optical Switches	10:45-12:15 Area 11: Micro/nano Electromechanical and Bio-Systems (Devices) C-8: Nano and Bio Sensors I	10:45-12:00 Area 10: Organic Materials Science, Device Physics, and Applications D-8: Organic Transistor I	10:45-12:15 Area 6: Compound Semiconductor Circuits, Electron Devices and Device Physics E-8: GaAs FETs and Process Technologies	10:45-12:25 Area 4: Advanced Memory Technology F-8: MRAM/PRAM	10:45-12:25 Area 2: Characterization and Materials Engineering for Interconnect Integration G-8: Special Session I ; Reliability	10:45-12:25 Area 3: CMOS Devices /Device Physics H-8: Advanced Channel and Substrate Technology	10:45-11:45 Area 8: Advanced Material Synthesis and Crystal Growth Technology I-8: Silicon-based Material Systems	10:45-12:25 Area 1: Advanced Gate Stack /Si Processing Science J-8: Metal/High-k CMOS
13:15-14:45 Area 9: Physics and Applications of Novel Functional Materials and Devices A-9: Novel Devices and Materials III	13:15-15:00 Area 7: Photonic Devices and Device Physics B-9: Detectors and Sensors	13:15-15:00 Area 11: Micro/nano Electromechanical and Bio-Systems (Devices) C-9: Nano and Bio Sensors II	13:30-15:00 Area 10: Organic Materials Science, Device Physics, and Applications D-9: Organic Transistor II	13:15-15:00 Area 6: Compound Semiconductor Circuits, Electron Devices and Device Physics E-9: GaN FETs and Process Technologies	13:15-14:55 Area 3: CMOS Devices /Device Physics F-9: Schottky S/D and Carrier Transport	13:15-15:35 Area 2: Characterization and Materials Engineering for Interconnect Integration G-9: Special SessionII ; Metallization Challenges	13:15-14:55 Area 3: CMOS Devices /Device Physics H-9: Carrier Transport		13:15-15:05 Area 1: Advanced Gate Stack /Si Processing Science J-9: Reliability
		15:15-16:30 Area 11: Micro/nano Electromechanical and Bio-Systems (Devices) C-10: MEMS and NEMS : Application	15:15-16:15 Area 10: Organic Materials Science, Device Physics, and Applications D-10: Organic Transistor III	15:15-17:00 Area 6: Compound Semiconductor Circuits, Electron Devices and Device Physics E-10: High-Voltage GaN Devices			15:15-16:55 Area 3: CMOS Devices /Device Physics H-10: Advanced Device Technology		15:15-16:35 Area 1: Advanced Gate Stack /Si Processing Science J-10: Metal Gate Electrode

## SSDM 2006 Advance Program General Information

### DATE

Conference: **September 13-15, 2006 (Official language is English)**  
Short Course: **September 12, 2006 (in Japanese)**

### LOCATION

#### Pacifico Yokohama

1-1-1 Minatomirai, Nishi-ku, Yokohama 220-0012, Japan  
Phone: +81-45-221-2155 Fax: +81-45-221-2136

Pacifico Yokohama, located in Yokohama's new and growing waterfront development Minato Mirai 21 area, is an integrated convention center on a world class scale. Since its opening in 1991, Pacifico Yokohama has hosted a variety of gatherings amid the magnificent surroundings of the international port city of Yokohama, Japan's historic window to the outside world.

It takes less than 2 hours from Tokyo international airport to Pacifico in limousine bus or train. From central Tokyo area, a 30 minutes ride on train will take you to Pacifico.

For further information, see  
<http://www.pacifico.co.jp/english/>

### REGISTRATION

The registration desk will be open from September 12 to 15 in the entrance hall on the third floor (conference site). The registration hours are as follows:

September 12	11:00-17:00	Foyer (5F)
13	9:00-17:00	Entrance Hall (2F)
14	9:00-17:00	Foyer (5F)
15	9:00-15:30	Foyer (5F)

**Early registration will be accepted only through the conference website until August 12, 2006, 24:00 Japan time.** (<http://www.ssdm.jp>)

Advanced registration through the conference website will be closed September 5, 2006, 17:00 Japan time. After the date, registration can be made at the conference site as on-site registration. Early registration is recommended.

	Registration Fee		Short Course (in Japanese)	Banquet
	On or Before 24:00, August 12 (Japan time)	On or After August 13		
Regular	¥40,000	¥45,000	¥15,000	¥7,000
Student	¥5,000		¥3,000	¥4,000
Accompanied person(s)				¥4,000/person

\* Fees include tax.

- 1) The registration fee includes one copy of the abstract book and a CD-ROM. However, it does not include the banquet, and an additional payment is required to attend the banquet (Regular: ¥7,000, Student/Accompanied person: ¥4,000).
- 2) Those who register as students are required to fax a copy of their current student ID to Kinki Nippon Tourist Co., Ltd. (KNT) (Fax: +81-3-5256-1588) at the time of registration and to present their student ID at the registration desk in order to be eligible for the student registration fee. When sending the fax, please write down your registration ID, which will be given at the completion of the online registration of individual information.
- 3) Registration is complete only after payment is made in full.

### Payment Procedure

Payment can be made by:

- One of the following credit cards:
  1. VISA
  2. MasterCard
  3. Diners Club
  4. American Express
  5. JCB
- A bank transfer to KNT Co., Ltd. (Message: SSDM)  
Account at Sumitomo Mitsui Banking Corp., Suzuran Branch, 1-3-12 Nishishimbashi, Minato-ku, Tokyo 105-0003, Japan (SWIFT Code: SMBCJPJT, Ordinary Account: 6103515, Account Name: Kinki Nippon Tourist Co., Ltd.)

\* Personal checks are not acceptable.

### Confirmation of Pre-Registration

Upon receipt of your online registration, a written confirmation will be faxed or e-mailed to you after your payment is confirmed.

Please bring this confirmation slip with you and present it to the registration desk.

### Registration Cancellation

Conference:

Cancellation fee of ¥3,000 will be deducted from the refund. Cancellation should be made in writing to KNT Co., Ltd. No cancellation will be accepted after August 17, 2006. Extended Abstracts will be sent to absent registrants after the conference.

Short Course:

Cancellation fee of ¥2,000 will be deducted from the refund. Cancellations should be made in writing to KNT Co., Ltd. No cancellation will be accepted after August 17. Short-course textbooks will be sent to the absent registrants after the conference.

Banquet:

Cancellation fee of ¥1,000 will be deducted from the refund, Cancellations should be made in writing to KNT Co., Ltd. No cancellation will be accepted after August. 17.

### Inquiries for Registration

Kinki Nippon Tourist Co., Ltd. (KNT)  
Global Business Management Branch  
Tokyo Kintetsu Bldg. 6F  
19-2 Kanda-Matsunaga-cho  
Chiyoda-ku  
Tokyo 101-8641, Japan  
Phone: +81-3-5256-1581  
Fax: +81-3-5256-1588  
E-mail: [ssdm2006-gb@or.knt.co.jp](mailto:ssdm2006-gb@or.knt.co.jp)  
Office hours: 9:30-17:30 (weekdays only)

### On-site Registration

Registration fees should be paid in Japanese Yen or credit cards. VISA, MasterCard, Diners Club, American Express and JCB are acceptable. No personal checks are acceptable.

### BANQUET

The conference banquet will be held on the evening of Wednesday, September 13. The banquet fee (Regular: ¥7,000, Student/Accompanied person: ¥4,000) is NOT included in the Registration fee. Participants who wish to attend the banquet are requested to order the banquet ticket through the on-line registration. Banquet tickets may also be purchased at the on-site registration desk.

### LATE NEWS PAPERS

Submission of Late News Papers has been already closed on July 31, 2006. The accepted papers will be on "Advance Program Part II" which will be distributed at the venue during the conference.

### SPECIAL Issue of JJAP

Authors of papers presented at SSDM 2006 are encouraged to submit the original to the Special Issue of the Japanese Journal of Applied Physics, which will be published in April 2007.

## **RUMP SESSIONS - September 14 (Thursday) 18:30-20:30**

### **Session A (Room 501, 5F)**

“Challenges of New Non-Volatile Memories: Innovative Strategies to catch up with FLASH”

Non-Volatile Memories (NVMs), in particular Flash, are playing an important role in the semiconductor market with usage in mobile phones and other types of mobile equipment. In the coming years mobile systems will demand even more NVM with high density and very high writing throughput for data storage application, or with fast random access for code execution. DRAM and NAND Flash, both of which occupy more than 70% of whole current memory market are expected to keep their fast technology evolution until 2015 and will reach at 20-30 nm technology node by the early of 2010s. If alternative NVMs such as FeRAM, MRAM, ReRAM and PRAM continue their technology evolution with the same speed as was done during last decade, there will be no chance to compete with NAND Flash in the future main memory market. Now as the scaling speeds of Flash and DRAM become slightly slow down, alternative NVMs might have a chance for the market. In this session, the material innovation of NVMs for catching up with the Flash Memories will be discussed.

Organizers/Moderators: N. Fujimura (Osaka Pref. Univ., Japan)  
T. Sakata (Hitachi, Japan)  
S. Zaima (Nagoya Univ., Japan)

Panelists: R. Bez/P. Cappelletti (STMicroelectronics, Italy)  
T. Ohta (Ovonic Phase Change Inst., Japan)  
Y. S. Park (Samsung Electronics, Korea)  
T. Shimoda (Seiko Epson, Japan) tentative  
H. Yoda (Toshiba, Japan) tentative

A couple of additional panelists will be invited.

### **Session B (Room 502, 5F)**

“Nanotechnology–Impact on Electronics, Photonics and Biology–”

Nanotechnology research is expanding its field rapidly, ranging from electronics, photonics, and mechanics to biology, and so on. However, it is still uncertain how it can be used and give real impacts on the fields, except some limited examples. From the fabrication point of view, the bottom-up technology and the top-down technology appear to be still separated, although a technology to make a bridge between them is highly required. From the functionality point of view, the single electronics, spintronics and quantum computing, et al., those discussed in terms of emerging research devices need nanotechnology to fabricate elemental devices for them. What are the new functionality of them? Can these new functional devices be fabricated in reality? Do they help the difficulty that the present silicon devices are facing? What are the biological application, and how it relates to electronics? There are many questions, most of which are difficult to answer. The rump session will begin with presentations from some panelists, followed by free discussions on these issues. We are grateful if audience may find their own answer through the session.

Organizers/Moderators: T. Ichiki (Univ. of Tokyo, Japan)  
K. Ishibashi (RIKEN, Japan)

Panelists: T. Fujisawa (NTT Corp., Japan)  
P. Hadley (Graz Univ. of Technology, Austria)  
T. Hiramoto (Univ. of Tokyo, Japan)  
J. Ohta (NAIST, Japan)  
M. Sugawara (Fujitsu Labs., Japan)  
H. Tabata (Osaka Univ., Japan)  
B. Yu (NASA Ames Research Center, USA)

## SHORT COURSE

Short Course entitled "Understanding Basic Physics of Scaled MOSFETs" will be held on Tuesday, September 12. All lectures are given in Japanese.

## AGREEMENT NOT TO PRE-PUBLISH ABSTRACTS

By submitting an abstract to the committee for review, the author(s) agrees that the work will not be published prior to presentation at the conference. Papers found to be in breach of this agreement will be withdrawn by the conference committee.

## AWARDS

"SSDM Awards" will be given to outstanding papers presented at previous conferences.

### SSDM Award

Given for an outstanding contribution to the field of solid state devices and materials, among papers presented prior to 2000.

### SSDM Paper Award

Given for the best paper presented at SSDM 2005.

### SSDM Young Researcher Award

Given for outstanding papers authored by young researchers and presented at SSDM 2005.

## FINANCIAL SUPPORT

Limited financial support is available for presentations by full-time students. Student presenters who are interested in support should contact the secretariat directly (e-mail: [ssdm@intergroup.co.jp](mailto:ssdm@intergroup.co.jp)) prior to the end of August after receiving their acceptance letter. A copy of their student ID should be submitted at application.

## TRAVEL GRANT

A travel grant is available for young researchers under 35 years old from overseas universities or public research institutes. The grant is available only to those whose abstracts are accepted, and who have applied for the grant. Submitting an application form does not guarantee that the grant will be awarded. Each related area chair will choose one candidate from the applicants. Late news papers are not eligible for travel grant.

The grant is authorized by the Marubun Research Promotion Foundation (MRPF), which is one of the cooperation organizations. The grant covers part of the recipient's travel costs, but does not necessarily cover all their expenses. Successful candidates must attend the ceremony which will be held during the conference (details of which will be given later) to receive the grant. Failure to attend will result in forfeiture of the grant.

## VISA REQUIREMENT

All foreign participants must have a valid passport. Participants from countries where a visa is required to enter Japan are advised to apply at the nearest Japanese Embassy or Consulate as soon as possible.

Concerning visa applications, generally, in applying for a visa each applicant is requested to submit the documents listed below:

- (1) an invitation letter (an optional document written in English)
- (2) a letter of guarantee (written in Japanese)
- (3) documents certifying the purpose of the visit (written in Japanese)
- (4) the applicant's schedule in Japan (written in Japanese)

Please ask the nearest Japanese Embassy to make sure what documents are required to obtain a visa first, and then contact the SSDM Secretariat. The Secretariat will send the Reply Form for Visa Application in order to obtain the required documents. Please complete the Reply Form for Visa Application and submit it to the Secretariat. We will send you all the requested documents as soon as we receive the Reply Form.

## OFFICIAL TRAVEL AGENT

Kinki Nippon Tourist Co., Ltd. (KNT)

Global Business Management Branch

Tokyo Kintetsu Bldg. 6F, 19-2 Kanda-Matsunaga-cho, Chiyoda-ku

Tokyo 101-8641, JAPAN

Phone: +81-3-5256-1581 Fax: +81-3-5256-1588

E-mail: [ssdm2006-gb@or.knt.co.jp](mailto:ssdm2006-gb@or.knt.co.jp)

## Hotel Accommodations

KNT has blocked rooms at following hotels in Yokohama for the conference period. Reservations can be made through the conference website.

Hotel Name	<b>Yokohama Grand Inter-continental Hotel</b>
Room Rates	Single: JPY23,100 Twin: JPY11,550 (per person, per night) *JPY2,100 will be added to the above rates on Sep. 15 (Fri.).
Hotel Deposit	JPY20,000
Check-in/out	Check-in:14:00/Check-out:11:00
Address	Minato Mirai 1-1-1 Nishi-ku, Yokohama-shi, Kanagawa 220-8522 Japan
Phone	+81-45-223-2222
Access to Hotel	2 min. walk from Minato Mirai Line Minato Miirai Sta.
To Conference site	Next to the site

Hotel Name	<b>Pan Pacific Hotel Yokohama</b>
Room Rates	Single: JPY21,000 Twin: JPY12,600 (per person, per night) *JPY3,150 for a single and JPY2,100 for a twin will be added to the above rates on Sep. 15 (Fri.)
Hotel Deposit	JPY20,000
Check-in/out	Check-in:14:00/Check-out:11:00
Address	Minato Mirai 2-3-7 Nishi-ku, Yokohama-shi, Kanagawa 220-8543 Japan
Phone	+81-45-682-2222
Access to Hotel	1 min. walk from Minato Mirai Line Minato Mirai Sta.
To Conference site	1 min. walk to the site

Hotel Name	<b>Navios Yokohama</b>
Room Rates	Single: JPY11,445 (per person, per night) *JPY1,050 will be added to the above rates on Sep. 15 (Fri.).
Hotel Deposit	JPY10,000
Check-in/out	Check-in:14:00/Check-out:10:00
Address	Shinko 2-1-1 Naka-ku, Yokohama-shi, Kanagawa 231-0001 Japan
Phone	+81-45-633-6000
Access to Hotel	3 min. walk from Minato Mirai Line? Bashamichi Sta.
To Conference site	7 min. walk to the site

Hotel Name	<b>Yokohama Sakuragicho Washington Hotel</b>
Room Rates	Single: JPY11,550 Twin: JPY8,925 (per person, per night)
Hotel Deposit	JPY10,000
Check-in/out	Check-in:14:00/Check-out:10:00
Address	Sakuragicho 1-1-67 Naka-ku, Yokohama-shi, Kanagawa 231-0062
Phone	+81-45-683-3111
Access to Hotel	3 min. walk from Minato Mirai Line Bashamichi Sta.
To Conference site	10 min. walk to the site



Hotel Name	<b>San-ai Yokohama Hotel</b>
Room Rates	Single: JPY9,240 (per person, per night)
Hotel Deposit	JPY10,000
Check-in/out	Check-in:14:00/Check-out:10:00
Address	Hanasakicho 3-95 Naka-ku, Yokohama-shi, Kanagawa 231-0063
Phone	+81-45-242-4411
Access to Hotel	5 min. walk from JR Sakuragicho sta.
To Conference site	15 min. walk to the site

- Notes: 1) All room rates are per person per night including breakfast, 10% service charge, and 5% consumption tax.  
2) The above rates are valid only during the period of the SSDM 2006 meeting.  
3) Communication fee of 500 JPY is required for per reservation and this is charged as handling charge for KNT.  
4) The deposit will be deducted from your hotel bill. Please settle the balance with the hotel cashier.  
5) The above rates and information are subject to change without notice.

### Application and Payment

Participants wishing to reserve hotel accommodations should access the Registration and Accommodation pages of the conference website. Reservations should be made by no later than August 18, 2006 (Japan time). (A confirmation sheet will be sent by KNT)

Application should be accompanied by the payment of room deposit and communication fee of 500 JPY.

No reservation will be confirmed in the absence of this payment. All payment must be paid only in Japanese yen by one of the following methods.

- 1) Credit Card:  
(VISA, MasterCard, Diners Club, AMEX or JCB only)  
\* Please fill in the necessary items with your signature in the credit card section of the application form.
- 2) Bank Transfer:  
Sumitomo Mitsui Banking Corp.  
Suzuran Branch  
SWIFT Code: SMBCJPJT  
Ordinary Account: 6103515  
Account Name: Kinki Nippon Tourist Co., Ltd.

### Cancellation Policy for Accommodations

In case of cancellation, a written notification should be sent to KNT by e-mail (ssdm2006-gb@or.knt.co.jp) or by FAX (+81-3-5256-1588) to avoid any trouble.

Hotels: Up to 14 days before the arrival date.No Charge  
13-7 days before.....10 % of daily room charge  
6-2 days before.....40 % of daily room charge  
Less than 2 days, or no notice given..100 % of daily room charge

### INSURANCE

The organizer cannot accept responsibility for accidents that may occur during a delegate's stay. Delegates are therefore encouraged to obtain travel insurance (medical, personal accident, and luggage) in their home countries prior to departure.

### CLIMATE

Yokohama is warm and sometimes humid in September. The temperature range is 18-30°C.

### ELECTRICAL APPLIANCES

Japan operates on 100 volts for electrical appliances. The frequency is 50 Hz in eastern Japan including Yokohama (conference site) and Tokyo, and 60 Hz in western Japan including Kyoto and Osaka.

## SSDM 2006 INSTRUCTION for SPEAKERS

### Oral Presentation

#### Time Schedule

	Session Time	Presentation	Discussion
Plenary	50 min.	45 min.	5 min.
Invited	30 min.	25 min.	5 min.
Regular-1	20 min.	15 min.	5 min.
Regular-2	15 min.	12 min.	3 min.

Buzzer First: Warning, Second: End of presentation, Third: End of discussion.

#### Audio-Visual Equipment

The meeting rooms will contain the following audiovisual equipment:

- LCD projector (**PC itself is not provided**)
- Overhead projector
- Microphone
- Projection laser pointer

Speakers wishing to present their papers using the LCD projector are requested to verify their PC's compatibility with the LCD projector at the conference room during a break time prior to their presentations.

#### Poster Presentation

Poster sessions are scheduled for Thursday, September 14, from 13:00 to 15:00. Poster boards will be available with identifying labels at the Room 501,502,511,512 on the fifth floor. Authors are requested to prepare their posters between 9:00 and 12:00 on September 14 and remove them by 15:30 on September 14. Any posters remaining after 15:30 will be disposed of by the secretariat. Usable space on each poster board will be approximately 900mm wide and 1,500mm high. Pushpins will be available. Each presentation will be assigned a board, labeled with the paper number. Please display the paper title, author names and affiliations on the poster. Authors are requested to stay near their posters during the poster session for discussions.

#### Short Oral Presentation for Poster Presenters

All poster presenters are asked to give a short oral presentation in the morning of September 14. The presentation time should be kept strictly to two minutes per poster presentation, including the time needed to move on to the next speaker. To ensure the session progresses smoothly, it is essential that these short presentations be held in a quick, successive sequence. While one speaker is giving his/her presentation, the next several speakers should wait nearby in line for their turn in order to move on to the next presentation. Note that any absent speakers will be skipped and each presentation will be automatically stopped after two minutes have elapsed. Only a PC projector will be made available. You should send your presentation file to the secretariat (ssdm@intergroup.co.jp) by e-mail by August 24. The file must be an exact "2-page" landscape PDF. Because the presentation time is limited, please describe your research objective and results clearly and do NOT show the author list or the title on your file, those of which will be prepared by the SSDM Secretariat.

Short oral presentations will be held, as follows. Please check your poster number. (P# means the poster presentation of Area #.)

Room 411/412	P11, P8
Room 413	P7, P4
Room 414/415	P5, P2
Room 416/417	P10
Room 418	P6, P9
Room 419	P3
Small Auditorium	P1